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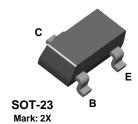
Jameco Part Number 783498



### 2N4401

### **MMBT4401**





### **NPN General Pupose Amplifier**

This device is designed for use as a medium power amplifier and switch requiring collector currents up to 500 mA.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6.0	V	
I <sub>C</sub>	Collector Current - Continuous	600	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max Units		
		2N4401	*MMBT4401	
$P_{D}$	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

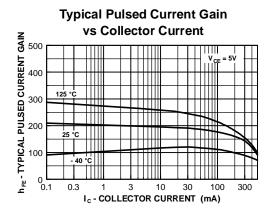
# NPN General Purpose Amplifier (continued)

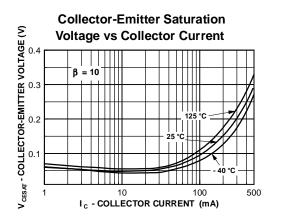
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 0.1 \text{ mA}, I_{\rm E} = 0$	60		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{ mA}, I_C = 0$	6.0		V
I <sub>BL</sub>	Base Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μΑ
I <sub>CEX</sub>	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μА
ON CHAR	ACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$	20		
		$I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40		
		$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	80		
		$I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100	300	
	Outleader Fusition Outlead in Maliana	$I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$	40	0.4	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$		0.4 0.75	V
\/	Base-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	0.75	0.75	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	1.2	V
SMALL SI	GNAL CHARACTERISTICS  Current Gain - Bandwidth Product	I <sub>C</sub> = 20 mA, V <sub>CE</sub> = 10 V, f = 100 MHz	250		MHz
C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_{E} = 0,$ f = 140 kHz		6.5	pF
C <sub>eb</sub>	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0,$ f = 140 kHz		30	pF
h <sub>ie</sub>	Input Impedance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0  kHz	1.0	15	kΩ
h <sub>re</sub>	Voltage Feedback Ratio	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0  kHz	0.1	8.0	x 10 <sup>-4</sup>
h <sub>fe</sub>	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	40	500	
h <sub>oe</sub>	Output Admittance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0  kHz	1.0	30	μmhos
SWITCHI	NG CHARACTERISTICS				
t <sub>d</sub>	Delay Time	$V_{CC} = 30 \text{ V}, V_{EB} = 2 \text{ V},$		15	ns
t <sub>r</sub>	Rise Time	$I_C = 150 \text{ mA}, I_{B1} = 15 \text{ mA}$		20	ns
t <sub>s</sub>	Storage Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA}$	+	225	ns
t <sub>f</sub>	Fall Time	$I_{B1} = I_{B2} = 15 \text{ mA}$		30	ns

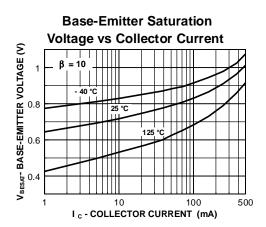
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

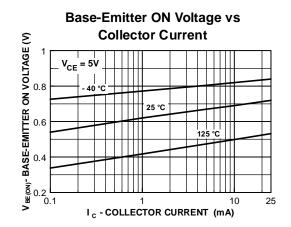
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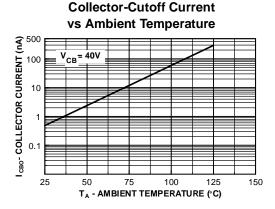
### **Typical Characteristics**

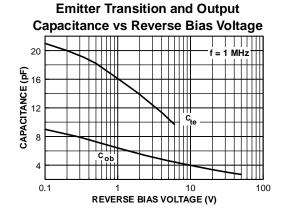








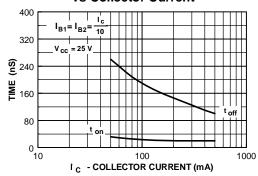




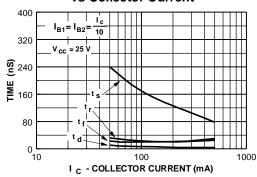
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### Typical Characteristics (continued)

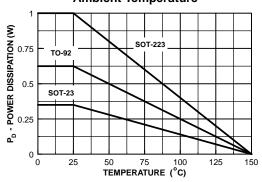
## Turn On and Turn Off Times vs Collector Current



## Switching Times vs Collector Current

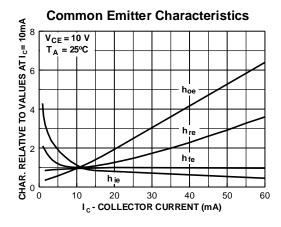


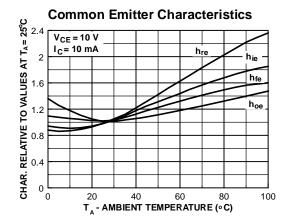
### Power Dissipation vs Ambient Temperature

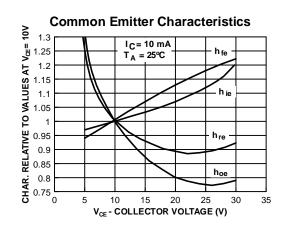


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### **Typical Common Emitter Characteristics** (f = 1.0kHz)







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### **Test Circuits**

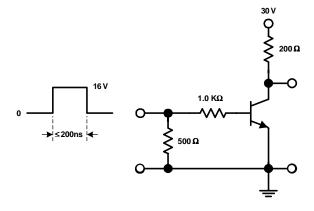


FIGURE 1: Saturated Turn-On Switching Timer

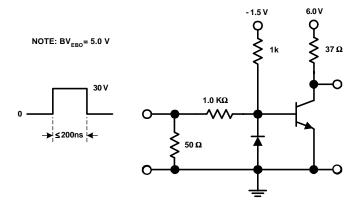


FIGURE 2: Saturated Turn-Off Switching Time

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